

Silicon NPN Power Transistors

2N5664 2N5665

DESCRIPTION

- With TO-66 package
- High breakdown voltage

APPLICATIONS

- High speed switching and linear amplifier
- High-voltage operational amplifiers
- Switching regulators ,converters
- Deflection stages and high fidelity amplifiers

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

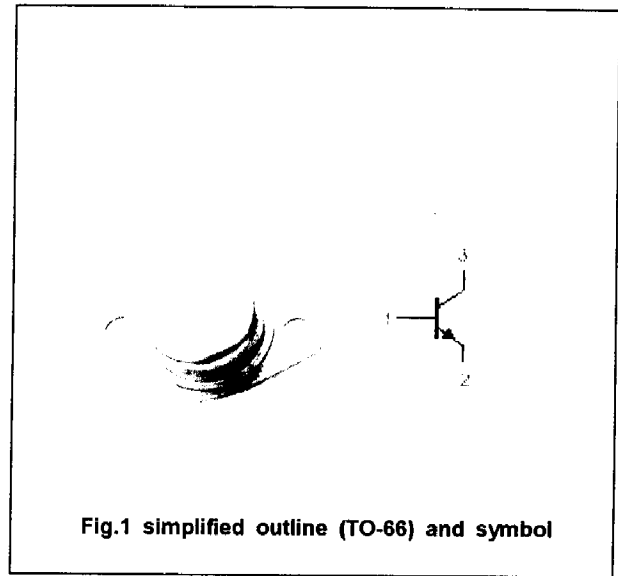


Fig.1 simplified outline (TO-66) and symbol

Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2N5664	250	V
		2N5665	400	
V _{CEO}	Collector-emitter voltage	2N5664	200	V
		2N5665	300	
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		5.0	A
I _B	Base current		1.0	A
P _T	Total power dissipation	T _C =25°C	52.5	W
T _J	Junction temperature		200	°C
T _{stg}	Storage temperature		-65~200	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th-jc}	Thermal resistance junction to case	5.0	°C/W

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